Photo Semiconductor Device - Page 1 of 1



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## Inclosure Material:

Metal

**Overall Length:** 

0.125 inches

# **Overall Diameter:**

0.093 inches

### Internal Configuration:

Junction contact

### **Mounting Method:**

Press fit

#### **Features Provided:**

Hermetically sealed case

#### Semiconductor Material:

Silicon

#### Voltage Rating In Volts Per Characteristic:

50.0 collector to emitter voltage/static/base open and 7.0 collector-to-emitter, resistance between base and emitter

### Power Rating Per Characteristic:

50.0 milliwatts small-signal input power, common-collector absolute

## Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction

## **Special Features:**

Junction pattern arrangement: npn

### **Terminal Type And Quantity:**

3 uninsulated wire lead

## Shelf Life:

N/a

#### Unit Of Measure:

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### Demilitarization:

No

#### Fiig:

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